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Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Logic level compatible
- · Very fast switching
- Trench MOSFET technology
- · Enhanced power dissipation capability of 1115 mW

## 3. Applications

- · Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                 | Parameter                        | Conditions  |     | Min | Тур | Max | Unit |
|------------------------|----------------------------------|---|-----|-----|-----|-----|------|
| $V_{DS}$               | drain-source voltage             | T <sub>j</sub> = 25 °C  |     | -   | -   | 30  | V    |
| $V_{GS}$               | gate-source voltage              |   |     | -20 | -   | 20  | V    |
| I <sub>D</sub>         | drain current                    | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s         | [1] | -   | -   | 5.6 | Α    |
| Static characteristics |                                  |   |     |     |     |     |      |
| R <sub>DSon</sub>      | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 4.5 \text{ A}; T_j = 25 \text{ °C}$ |     | -   | 31  | 36  | mΩ   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline      | Graphic symbol |
|-----|--------|-------------|-------------------------|----------------|
| 1   | G      | gate        | <u></u> 3               | D<br>I         |
| 2   | S      | source      |                         |                |
| 3   | D      | drain       |                         | G T            |
|     |        |             | 1 2<br>TO-236AB (SOT23) | 017aaa253      |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number | Package  |  |         |  |  |  |
|-------------|----------|--|---------|--|--|--|
|             | Name     | Description                              | Version |  |  |  |
| PMV37EN2    | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |  |  |  |

## 7. Marking

#### Table 4. Marking codes

| Type number | Marking code <sup>[1]</sup> |
|-------------|-----------------------------|
| PMV37EN2    | %K7                         |

[1] % = placeholder for manufacturing site code

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## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  |     | Min | Max  | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| $V_{DS}$         | drain-source voltage    | T <sub>j</sub> = 25 °C                                    |     | -   | 30   | V    |
| V <sub>GS</sub>  | gate-source voltage     |   |     | -20 | 20   | V    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s | [1] | -   | 5.6  | Α    |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C          | [1] | -   | 4.5  | Α    |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C         | [1] | -   | 2.8  | Α    |
| I <sub>DM</sub>  | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$       |     | -   | 16   | Α    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C                                  | [2] | -   | 510  | mW   |
|                  |                         |   | [1] | -   | 1115 | mW   |
|                  |                         | T <sub>sp</sub> = 25 °C                                   |     | -   | 5000 | mW   |
| T <sub>j</sub>   | junction temperature    |   |     | -55 | 150  | °C   |
| T <sub>amb</sub> | ambient temperature     |   |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature     |   |     | -65 | 150  | °C   |
| Source-drain     | diode                   |   |     |     |      |      |
| I <sub>S</sub>   | source current          | T <sub>amb</sub> = 25 °C                                  | [1] | -   | 1    | Α    |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

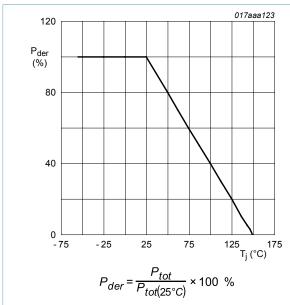


Fig. 1. Normalized total power dissipation as a function of junction temperature

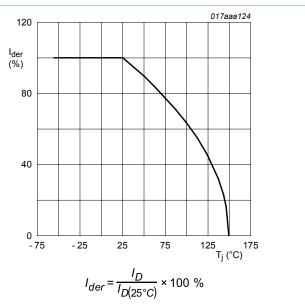
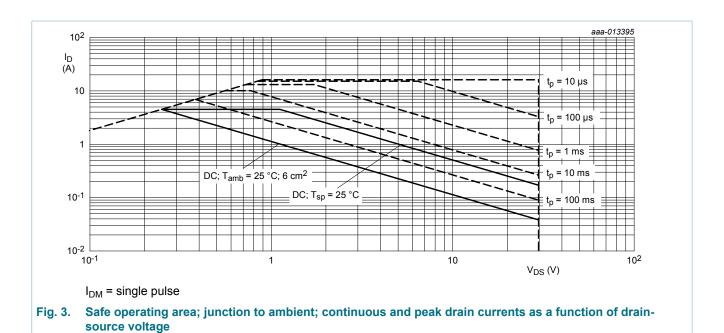


Fig. 2. Normalized continuous drain current as a function of junction temperature

#### 30 V, N-channel Trench MOSFET



### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

| Symbol                | Parameter   | Conditions           |     | Min | Тур | Max | Unit |
|-----------------------|---|----------------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient | III II EE ali        | [1] | -   | 209 | 246 | K/W  |
|                       |   |                      | [2] | -   | 95  | 112 | K/W  |
|                       |   | in free air; t ≤ 5 s | [2] | -   | 63  | 72  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point  |                      |     | -   | 20  | 25  | K/W  |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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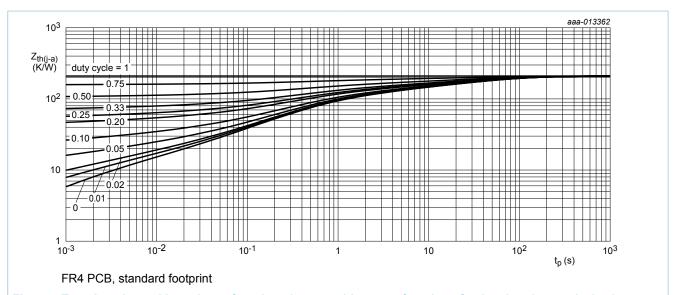


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

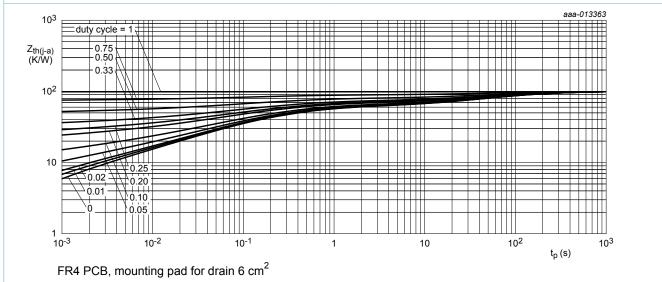


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### **Table 7. Characteristics**

| Symbol              | Parameter                         | Conditions  | Min | Тур  | Max  | Unit |
|---------------------|-----------------------------------|---|-----|------|------|------|
| Static char         | acteristics                       |   |     |      |      |      |
| $V_{(BR)DSS}$       | drain-source<br>breakdown voltage | $I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C                      | 30  | -    | -    | V    |
| $V_{GSth}$          | gate-source threshold voltage     | $I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C                | 1   | 1.5  | 2    | V    |
| I <sub>DSS</sub>    | drain leakage current             | V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -    | 1    | μΑ   |
| I <sub>GSS</sub>    | gate leakage current              | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -    | 100  | nA   |
|                     |                                   | $V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                         | -   | -    | -100 | nA   |
| DOON                | drain-source on-state             | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4.5 A; T <sub>j</sub> = 25 °C  | -   | 31   | 36   | mΩ   |
|                     | resistance                        | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4.5 A; T <sub>j</sub> = 150 °C | -   | 48   | 56   | mΩ   |
|                     |                                   | $V_{GS}$ = 4.5 V; $I_D$ = 3.9 A; $T_j$ = 25 °C                          | -   | 37   | 47   | mΩ   |
| 9 <sub>fs</sub>     | forward transconductance          | $V_{DS} = 10 \text{ V}; I_D = 2 \text{ A}; T_j = 25 \text{ °C}$         | -   | 13   | -    | S    |
| R <sub>G</sub>      | gate resistance                   | T <sub>j</sub> = 25 °C; f = 1 MHz                                       | -   | 2.3  | -    | Ω    |
| Dynamic c           | haracteristics                    |   |     |      |      |      |
| Q <sub>G(tot)</sub> | total gate charge                 | $V_{DS}$ = 15 V; $I_D$ = 3.2 A; $V_{GS}$ = 10 V;                        | -   | 3.6  | 6.3  | nC   |
| $Q_{GS}$            | gate-source charge                | T <sub>j</sub> = 25 °C  | -   | 0.5  | -    | nC   |
| $Q_{GD}$            | gate-drain charge                 |   | -   | 0.4  | -    | nC   |
| C <sub>iss</sub>    | input capacitance                 | V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;               | -   | 209  | -    | pF   |
| C <sub>oss</sub>    | output capacitance                | T <sub>j</sub> = 25 °C  | -   | 50   | -    | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance      |   | -   | 17   | -    | pF   |
| t <sub>d(on)</sub>  | turn-on delay time                | V <sub>DS</sub> = 15 V; I <sub>D</sub> = 3.2 A; V <sub>GS</sub> = 10 V; | -   | 3    | -    | ns   |
| t <sub>r</sub>      | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$                             | -   | 12   | -    | ns   |
| t <sub>d(off)</sub> | turn-off delay time               |   | -   | 11   | -    | ns   |
| t <sub>f</sub>      | fall time                         |   | -   | 2    | -    | ns   |
| Source-dra          | ain diode                         |   | 1   | ,    | ,    | ,    |
| $V_{SD}$            | source-drain voltage              | I <sub>S</sub> = 1 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C     | _   | 0.75 | 1.2  | V    |

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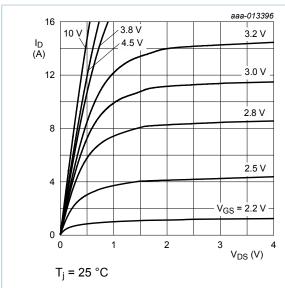


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

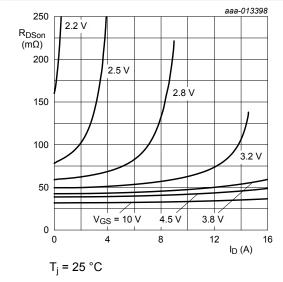


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

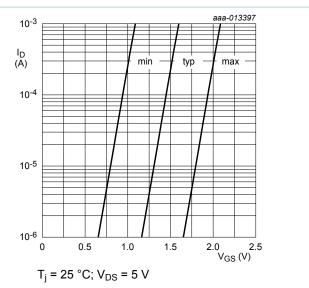


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

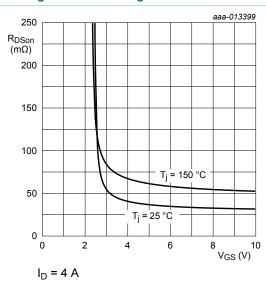


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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#### 30 V, N-channel Trench MOSFET

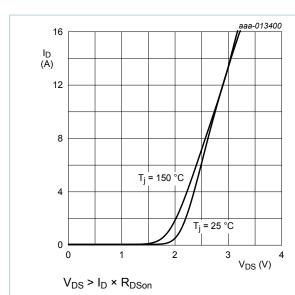


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

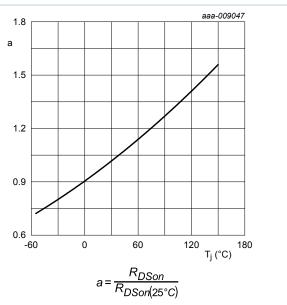


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

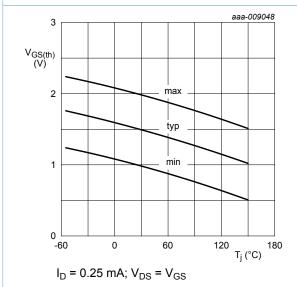


Fig. 12. Gate-source threshold voltage as a function of junction temperature

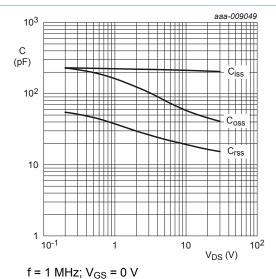


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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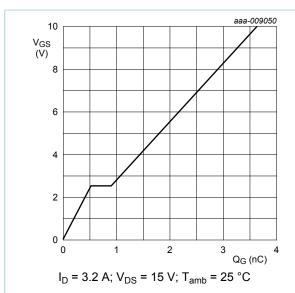


Fig. 14. Gate-source voltage as a function of gate charge; typical values

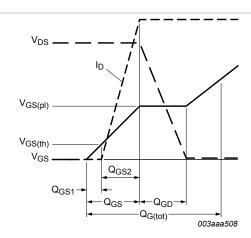


Fig. 15. MOSFET transistor: Gate charge waveform definitions

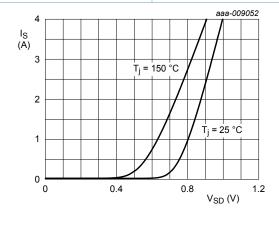
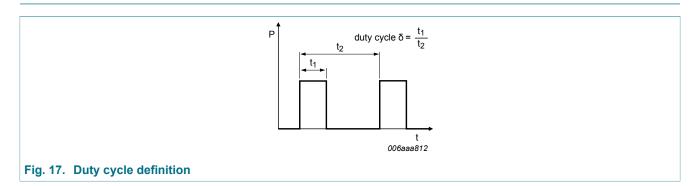


Fig. 16. Source current as a function of source-drain voltage; typical values

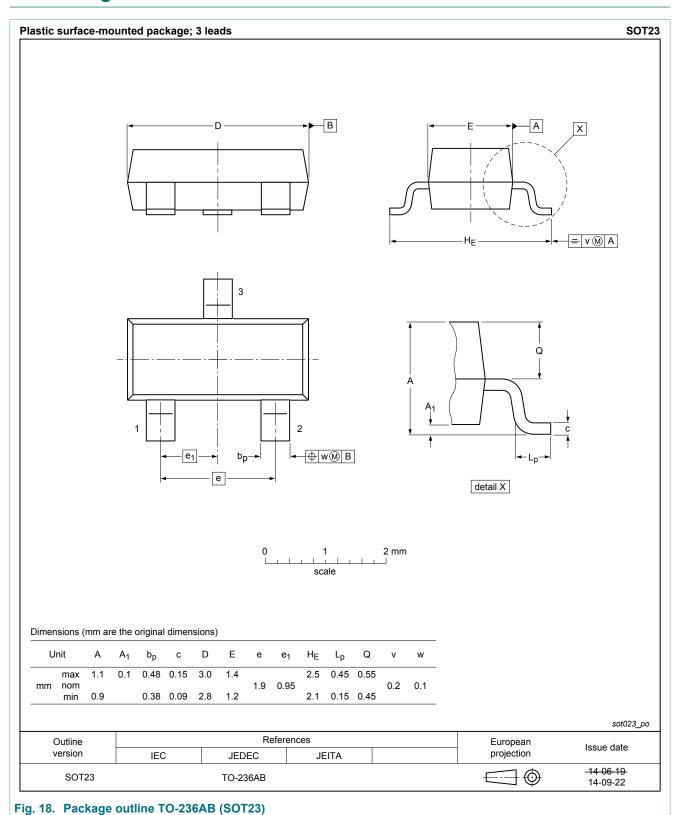
## 11. Test information

 $V_{GS} = 0 V$ 



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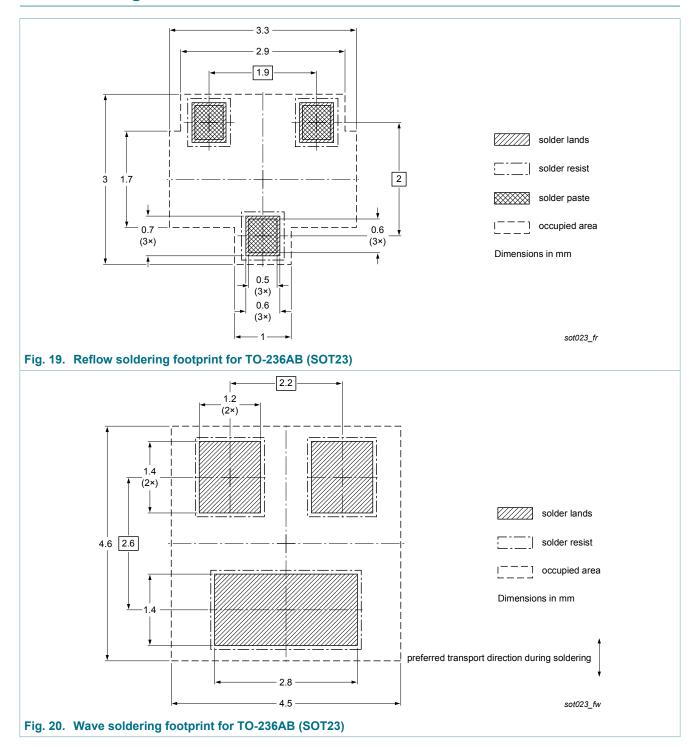
## 12. Package outline



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## 13. Soldering



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# 14. Revision history

### **Table 8. Revision history**

| Data sheet ID  | Release date   | Data sheet status  | Change notice | Supersedes   |  |  |  |  |
|----------------|--|--------------------|---------------|--------------|--|--|--|--|
| PMV37EN2 v.2   | 20170110   | Product data sheet | -             | PMV37EN2 v.1 |  |  |  |  |
| Modifications: | Section 10. Characteristics: values for forward transconductance and gate resistance changed |                    |               |              |  |  |  |  |
| PMV37EN2 v.1   | 20140603   | Product data sheet | -             | -            |  |  |  |  |

#### 30 V, N-channel Trench MOSFET

# 15. Legal information

#### **Data sheet status**

| Document status [1] [2]              | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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| Product<br>[short] data<br>sheet     | Production         | This document contains the product specification.                                     |

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PMV37EN2

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### 30 V, N-channel Trench MOSFET

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